

L Number	Hits	Search Text	DB	Time stamp
1	58	(Ge or Germanium) same (nucleat\$3 adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/12 08:23
2	36	(Ge or Germanium) with (nucleat\$3 adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/12 08:23
3	389	MEMS and etch\$3 and (sacrificial).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/12 09:10
-	761	(216/2).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 12:23
-	87	((216/2).CCLS.) and (Ge or Germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 17:35
-	4290	(MEMS or micromechanical or microelectromechanical or microstructure\$1) and (Ge or Germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/13 13:09
-	2	((MEMS or micromechanical or microelectromechanical or microstructure\$1) and (Ge or Germanium)).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 12:39
-	115	((MEMS or micromechanical or microelectromechanical or microstructure\$1) and (Ge or Germanium)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 12:25
-	179	((MEMS or micromechanical or microelectromechanical or microstructure\$1) and (Ge or Germanium)).ab.) or ((MEMS or micromechanical or microelectromechanical or microstructure\$1) and (Ge or Germanium)).ti.) or ((MEMS or micromechanical or microelectromechanical or microstructure\$1) and (Ge or Germanium)).clm.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 12:26
-	22	(MEMS or micromechanical or microelectromechanical or microstructure\$1) and ((Ge or Germanium) same (protect\$3 adj (coating or layer or material or film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 12:33
-	23	(MEMS or micromechanical or microelectromechanical or microstructure\$1) and ((Ge or Germanium) and (protect\$3 adj (coating or layer or material or film))).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 12:34
-	23	(MEMS or micromechanical or microelectromechanical or microstructure\$1).ab. and (Ge or Germanium) and (protect\$3 adj (coating or layer or material or film)).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 12:43

-	44	((MEMS or micromechanical or microelectromechanical or microstructure\$1) and ((Ge or Germanium) and (protect\$3 adj (coating or layer or material or film)).clm.) or ((MEMS or micromechanical or microelectromechanical or microstructure\$1).ab. and (Ge or Germanium) and (protect\$3 adj (coating or layer or material or film)).ab.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/13 13:09
-	75	((MEMS or micromechanical or microelectromechanical or microstructure\$1) and (Ge or Germanium)).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/05 14:08
-	960	((Ge or Germanium) and (protect\$3 adj (coating or layer or material or film)).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/13 13:09
-	3	((Ge or Germanium) and (temporary or removable) and (protect\$3 adj (coating or layer or material or film))).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 12:45
-	14	((216/2).CCLS.) and (Ge or Germanium) and (protect\$3 adj (coating or layer or material or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 12:47
-	32	(MEMS or micromechanical or microelectromechanical or microstructure\$1) and (Ge or Germanium) and (protect\$3 adj (coating or layer or material or film)) and ((polysilicon or nucleat\$3) adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/05 14:09
-	44	((Ge or Germanium) same (protect\$3 adj (coating or layer or material or film))) and ((polysilicon or nucleat\$3) adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/12 08:22
-	40	(temporary adj protective) and (Ge or Germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 13:23
-	99	(removable adj protective) and (Ge or Germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 13:30
-	10	((Ge or Germanium) and (protect\$3 adj (coating or layer or material or film)).ab. and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/05 12:37
-	3	((Ge or Germanium) and (protect\$3 adj (coating or layer or material or film)).ab. and (MEMS or micromechanical or microelectromechanical or microstructure\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 13:28
-	113	((Ge or Germanium) and (protect\$3 adj (coating or layer or material or film))) and (front adj side) and (back adj side)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/05 12:38
-	8	(MEMS or micromechanical or microelectromechanical or microstructure\$1).ab. and ((Ge or Germanium) adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/05 12:47

-	81	(MEMS or micromechanical or microelectromechanical or microstructure\$1) and ((Ge or Germanium) adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/11 16:42
-	2455	(MEMS or micromechanical or microelectromechanical or microstructure\$1) and ((back adj side) or back-side or backside)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/05 12:56
-	255	(MEMS or micromechanical or microelectromechanical or microstructure\$1) and ((back adj side) or back-side or backside).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/05 13:32
-	7	((yaw adj rate) or acceleration) with sensor).ab. and ((back adj side) or back-side or backside).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/05 13:34
-	40	(pressure with sensor).ab. and ((back adj side) or back-side or backside).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/05 13:36
-	4	(MEMS and sensor).ab. and ((back adj side) or back-side or backside).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/05 13:37
-	10	(MEMS and sensor).ab. and etch\$3.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/05 13:37
-	92	(accelerometer).ab. and etch\$3.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/05 13:37
-	3	(accelerometer).ab. and ((back adj side) or back-side or backside).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/05 14:33
-	2	("6368885").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/05 14:08
-	6	("5527744" "5903380" "6080675" "6140689" "6204087" "6225145").PN.	USPAT;	2003/12/05 14:08
-	2889	(MEMS or micromechanical or microelectromechanical or microstructure\$1) and (protect\$3 adj (coating or layer or material or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/05 14:11
-	646	(MEMS or micromechanical or microelectromechanical or microstructure\$1) and (protect\$3 adj (coating or layer or material or film)) and sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/05 14:33
-	60	(diaphragm and cavity).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/05 14:33
-	141	(transducer\$1).ab. and ((back adj side) or back-side or backside).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/05 14:35

-	99	(transducer\$1).ab. and ((recess or cavity) and etch\$3).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/05 14:36
-	215	(427/155).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/13 13:05
-	318	(427/156).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/13 13:06
-	11	((427/154).CCLS.) and (Ge or Germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/13 13:07
-	413	(427/154).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/13 13:07
-	17	((427/155).CCLS.) or ((427/156).CCLS.) or ((427/154).CCLS.) and (Ge or Germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/13 13:07
-	415	(MEMS or micromechanical or microelectromechanical or microstructure\$1) and (Ge or Germanium) and (protect\$3 adj (coating or layer or material or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/13 13:10
-	208	(MEMS or micromechanical or microelectromechanical or microstructure\$1) and (protect\$3 adj (coating or layer or material or film) and mask\$3.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/13 13:12
-	156	(MEMS or micromechanical or microelectromechanical or microstructure\$1) and (protect\$3 adj (coating or layer or material or film)) and (SOI or silicon-on-insulator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/13 13:13
-	523	(MEMS or micromechanical or microelectromechanical or microstructure\$1) and (protect\$3 adj (coating or layer or material or film)).clm. and (pattern\$3 or etch\$3 or remov\$3 or form\$3).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/13 14:44
-	62	(MEMS or micromechanical or microelectromechanical or microstructure\$1).ti. and (protect\$3 adj (coating or layer or material or film)).clm. and (pattern\$3 or etch\$3 or remov\$3 or form\$3).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/13 13:31
-	0	(MEMS or micromechanical or microelectromechanical or microstructure\$1).ti. and (release adj mask).clm. and (pattern\$3 or etch\$3 or remov\$3 or form\$3).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/13 13:53
-	283	(MEMS or micromechanical or microelectromechanical or microstructure\$1) and (protective adj layer).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/13 13:47
-	4	(("5627317") or ("5574222")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/13 13:47

-	89	(germanium with mask).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/13 13:55
-	62	(MEMS or micromechanical or microelectromechanical or microstructure\$1) and ((pattern\$3 or etch\$3 or remov\$3 or form\$3) with (backside or back-side)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/13 14:50
-	102	(sensor\$1 or transducer\$1).clm. and ((pattern\$3 or etch\$3 or remov\$3 or form\$3) with (backside or back-side)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/13 14:51
-	898	257/419	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/13 15:07
-	215	((MEMS or micromechanical or microelectromechanical or microstructure\$1) and (protective or sacrificial) and (mask\$3 or oxide or polysilicon)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/11 17:23
-	15	((("5798283") or ("5504026") or ("5847280") or ("5326726") or ("5343064") or ("5747353") or ("5506175") or ("5576250")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/11 17:25
-	33	((216/2).CCLS.) and (MEMS).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/11 17:37
-	114	((216/2).CCLS.) and MEMS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/11 17:38
-	8783	MEMS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/11 17:48
-	4380	MEMS and etch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/11 17:49
-	1098	MEMS and etch\$3 and (release or sacrificial or mask\$3 or protect\$3).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/12 09:09
-	57	(MEMS and etch\$3 and (release or sacrificial or mask\$3 or protect\$3).clm.) and (backside or back-side or (back adj side)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/01/11 17:51